



N-CHANNEL ENHANCEMENT MODE MOSFET

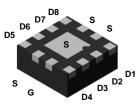
Features

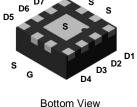
- Low Gate Charge
- $R_{DS(ON)}$: 280m Ω @ V_{GS} = 4.5V (Single MOSFET)
- 8 N-Channel MOSFET in One Package
- Common Source
- Small Footprint 1.5mm x 1.5mm
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

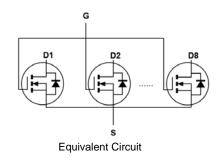
Mechanical Data

- Case: U-QFN1515-12
- Case Material-Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Terminal Connections: See Diagram
- Weight: 0.004 grams (Approximate)

U-QFN1515-12







Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1250UFEL-7	U-QFN1515-12	3000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

U-QFN1515-12



A1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: B = 2014)M = Month (ex: 8 = August)

Date Code Key

Year	2014		2015	2016		2017	2018		2019	2020		2021
Code	В		С	D		E	F		G	Н		1
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V _{DSS}	12	V
Gate-Source Voltage		V _{GSS}	±8	V
Drain Current (Note 6) Continuous	$T_A = +25$ °C $T_A = +70$ °C		2.0 1.6	Α
Pulsed Drain Current (Note 7)		I _{DM}	10	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.66	W
Total Power Dissipation (Note 6)	P _D	1.25	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{ÐJA}	177	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{OJA}	100	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- Device mounted on 1" x 1", FR-4 PC board with minimum recommended pad layout, and test with single MOSFET.
 Device mounted on 1" x 1", FR-4 PC board with 2 oz. copper, and test with single MOSFET.
 Repetitive Rating, pulse width limited by junction temperature, and test with single MOSFET.

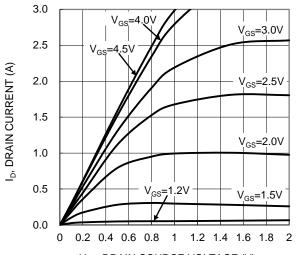
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
STATIC CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	12		_	V	$I_D = 250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_		1	μΑ	$V_{DS} = 12V, V_{GS} = 0V$	
Gate-Body Leakage Current	I _{GSS}	_		±100	nA	$V_{DS} = 0V$, $V_{GS} = \pm 8V$	
Gate Threshold Voltage	V _{GS(TH)}	0.4		1	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance (Note 8)	D- avays	_	280	450	mΩ	$V_{GS} = 4.5V, I_D = 0.2A$	
Static Dialif-Source Off-Resistance (Note 8)	R _{DS(ON)}	_	360	550	mΩ	$V_{GS} = 2.5V, I_D = 0.1A$	
Forward Transfer Admittance	Y _{FS}	_	1		S	$V_{DS} = 6V, I_D = 0.2A$	
Diode Forward Voltage (Note 8)	V_{SD}	_	0.8	1.0	V	$I_S = 0.2A, V_{GS} = 0V$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	146	190	pF		
Output Capacitance	Coss	_	10	15	pF	$V_{DS} = 6V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	8	13	pF	1 = 1.0ivii 12	
Gate Resistance	R_{G}	_	2.4	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$	
SWITCHING CHARACTERISTICS (Note 9)							
Total Gate Charge	Q_g	_	1.3	1.9	nC		
Gate-Source Charge	Q_gs	_	0.3	_	nC	$V_{GS} = 4.5V$, $V_{DS} = 6V$, $I_{D} = 0.2A$	
Gate-Drain Charge	Q_gd	_	0.1	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	1.9	2.7	nS		
Turn-On Rise Time	t _R		1.3	_	nS	$V_{DD} = 6V, V_{GS} = 4.5V,$	
Turn-Off Delay Time	t _{D(OFF)}	_	7.5	11	nS	$R_L = 22\Omega$, $R_G = 6\Omega$	
Turn-Off Fall Time	t _F		1.0	_	nS		

- 8. Test pulse width t = 300ms, test with single MOSFET.
 9. Guaranteed by design with single MOSFET, not subject to production testing.







V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 1. Typical Output Characteristic

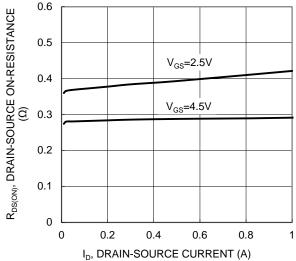


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

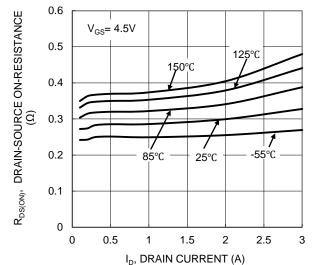
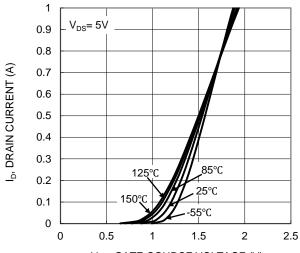


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic

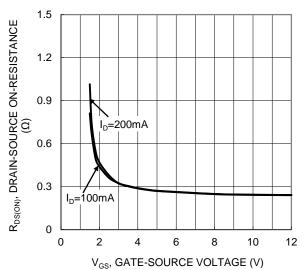


Figure 4. Typical Transfer Characteristic

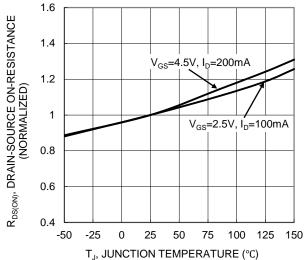
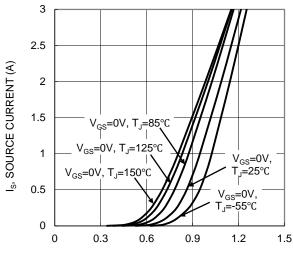


Figure 6. On-Resistance Variation with Temperature

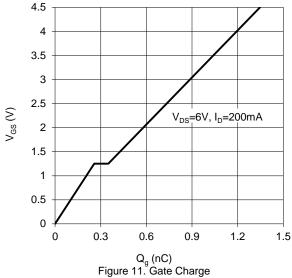


0.6 R_{DS(ON)}, DRAIN-SOURCE ON-RESISTANCE $V_{GS} = 2.5 V, I_{D} = 100 mA$ 0.4 V_{GS} =4.5V, I_D =200mA 0.2 0 -50 -25 0 25 50 75 100 125 150 T_.I, JUNCTION TEMPERATURE (°C)

Figure 7. On-Resistance Variation with Temperature



 V_{SD} , SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current



DMN1250UFEL

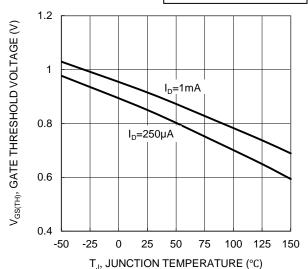
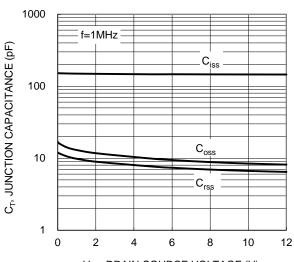
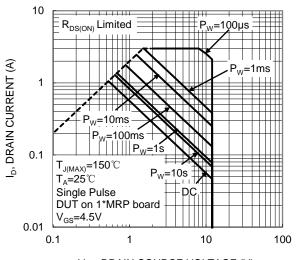


Figure 8. Gate Threshold Variation vs. Junction Temperature

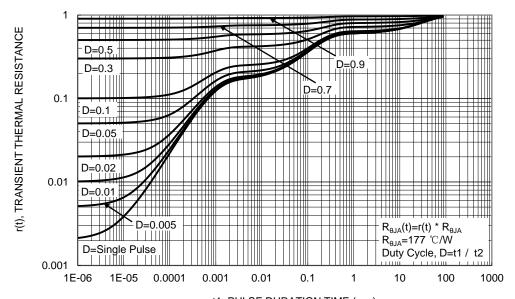


 V_{DS} , DRAIN-SOURCE VOLTAGE (V) Figure 10. Typical Junction Capacitance



V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area





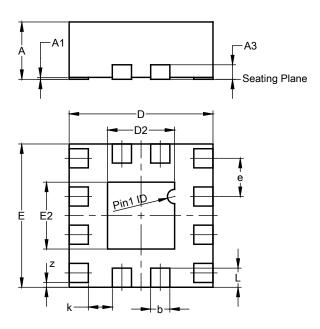
t1, PULSE DURATION TIME (sec) Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

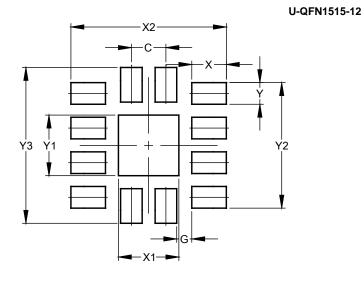
U-QFN1515-12



U-QFN1515-12						
Dim	Min	Max	Тур			
Α	0.57	0.63	0.60			
A1	0.00	0.05	0.02			
А3	0.152 BSC					
b	0.15	0.25	0.20			
D	1.45	1.55	1.50			
D2	0.60	0.80	0.70			
Е	1.45	1.55	1.50			
E2	0.60	0.80	0.70			
е	0.40 BSC					
L	0.15	0.25	0.20			
k		_	0.25			
Z		_	0.050			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value		
Dillielisions	(in mm)		
С	0.400		
G	0.175		
X	0.400		
X1	0.700		
X2	1.800		
Y	0.250		
Y1	0.700		
Y2	1.450		
Y3	1.800		



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